

**2N4220  
thru  
2N4222**

**2N4220,A  
thru  
2N4222,A**

**CASE 20-03, STYLE 3  
TO-72 (TO-206AF)**

**JFET  
LOW-FREQUENCY, LOW NOISE**

**N-CHANNEL — DEPLETION**

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>D</sub> S	30	Vdc
Drain-Gate Voltage	V <sub>DG</sub>	30	Vdc
Gate-Source Voltage	V <sub>GS</sub>	-30	Vdc
Drain Current	I <sub>D</sub>	15	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2	mW mW/°C
Junction Temperature Range	T <sub>J</sub>	175	°C
Storage Channel Temperature Range	T <sub>stg</sub>	-65 to +200	°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

**6**

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Gate-Source Breakdown Voltage (I <sub>G</sub> = -10 μAdc, V <sub>DS</sub> = 0)	V <sub>(BR)GSS</sub>	-30	—	—	Vdc
Gate Reverse Current (V <sub>GS</sub> = -15 Vdc, V <sub>DS</sub> = 0) (V <sub>GS</sub> = -15 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>GSS</sub>	— —	— —	-0.1 -100	nAdc
Gate Source Cutoff Voltage (I <sub>D</sub> = 0.1 nAdc, V <sub>DS</sub> = 15 Vdc)	V <sub>GS(off)</sub>	— — —	— — —	-4 -6 -8	Vdc
Gate Source Voltage (I <sub>D</sub> = 50 μAdc, V <sub>DS</sub> = 15 Vdc) (I <sub>D</sub> = 200 μAdc, V <sub>DS</sub> = 15 Vdc) (I <sub>D</sub> = 500 μAdc, V <sub>DS</sub> = 15 Vdc)	V <sub>GS</sub>	— — —	-0.5 -1.0 -2.0	-2.5 -5.0 -6.0	Vdc
<b>ON CHARACTERISTICS</b>					
Zero-Gate-Voltage Drain Current* (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	0.5 2.0 5.0	— — —	3.0 6.0 15	mAdc
Static Drain-Source On Resistance (V <sub>DS</sub> = 0, V <sub>GS</sub> = 0)	r <sub>DS(on)</sub>	— — —	500 400 300	— — —	Ohms

**SMALL-SIGNAL CHARACTERISTICS**

Forward Transfer Admittance Common Source* (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	2N4220,A 2N4221,A 2N4222,A	y <sub>fs</sub>	1000 2000 2500	— — —	4000 5000 6000	μhos
Output Admittance Common Source (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	2N4220,A 2N4221,A 2N4222,A	y <sub>os</sub>	— — —	— — —	10 20 40	μhos
Input Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	—	4.5	6.0	pF	
Reverse Transfer Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>rss</sub>	—	1.2	2.0	pF	
Common-Source Output Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 30 MHz)	C <sub>osp</sub>	—	1.5	—	pF	

## 2N4220 thru 2N4222, 2N4220A thru 2N4222A

ELECTRICAL CHARACTERISTICS (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>FUNCTIONAL CHARACTERISTICS</b>					
Noise Figure ( $V_{DS} = 15 \text{ Vdc}$ , $V_{GS} = 0$ , $R_S = 1.0 \text{ megohm}$ , $f = 100 \text{ Hz}$ )	NF	—	—	2.5	dB
2N4220A		—	—	2.5	
2N4221A		—	—	2.5	
2N4222A		—	—	2.5	

\*Pulse Test: Pulse Width = 630 ms, Duty Cycle = 10%.

FIGURE 1 — NOISE FIGURE versus FREQUENCY

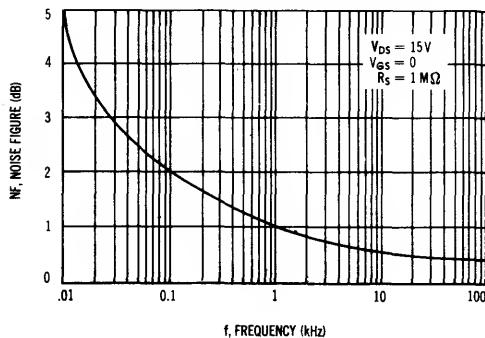


FIGURE 2 — NOISE FIGURE versus SOURCE RESISTANCE

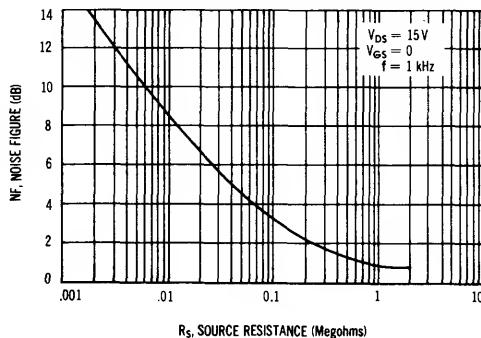


FIGURE 3 — TYPICAL DRAIN CHARACTERISTICS  
 $V_{GS(\text{off})} \approx -1.2 \text{ VOLTS}$

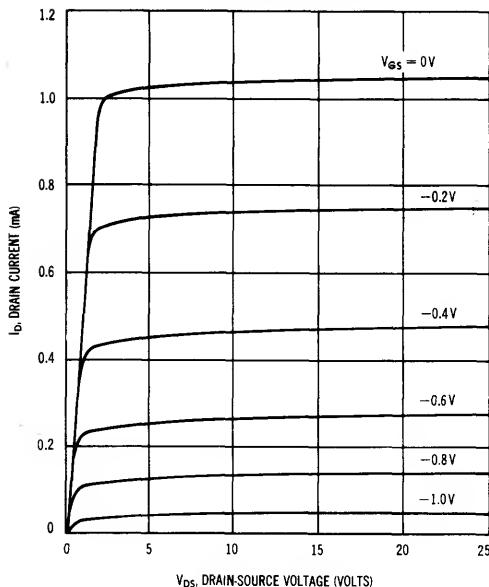
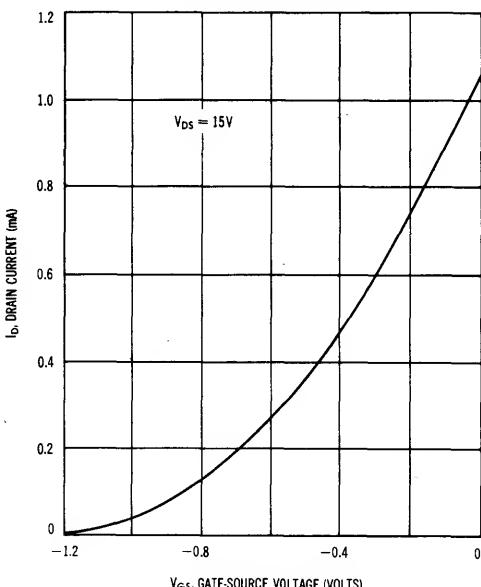
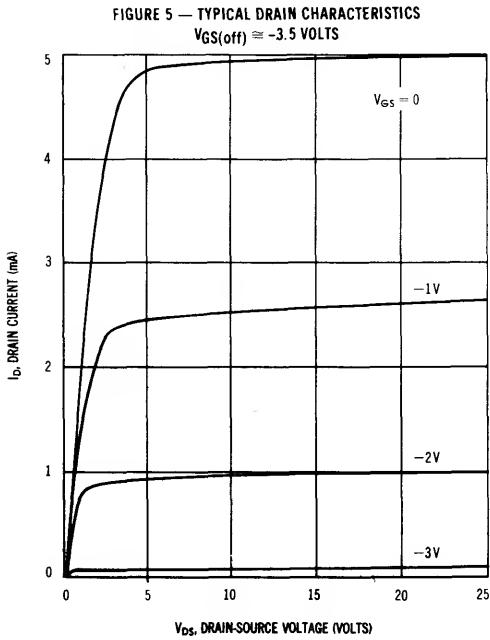


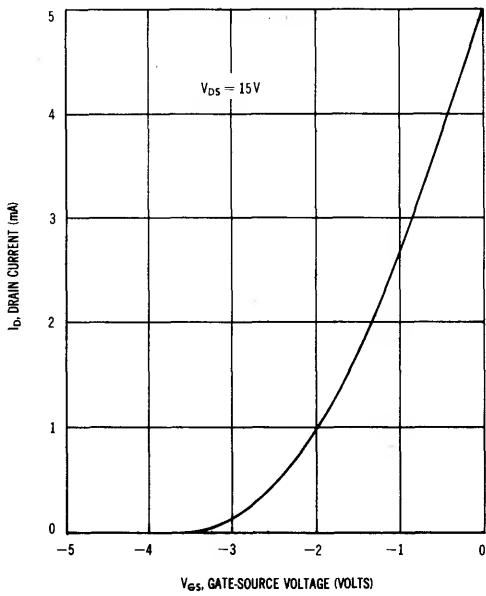
FIGURE 4 — COMMON SOURCE TRANSFER CHARACTERISTICS  
 $V_{GS(\text{off})} \approx -1.2 \text{ VOLTS}$



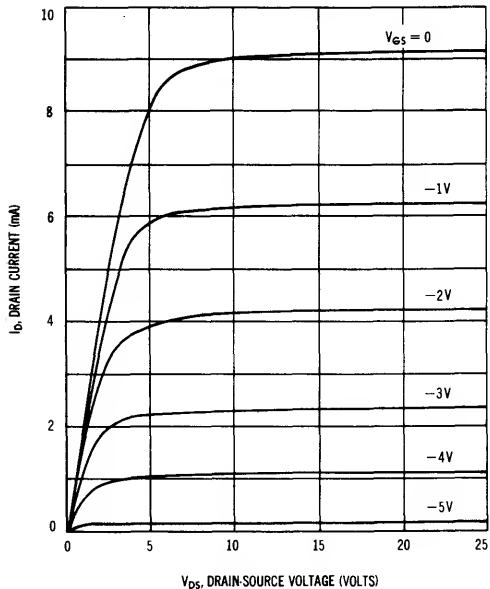
**2N4220 thru 2N4222, 2N4220A thru 2N4222A**



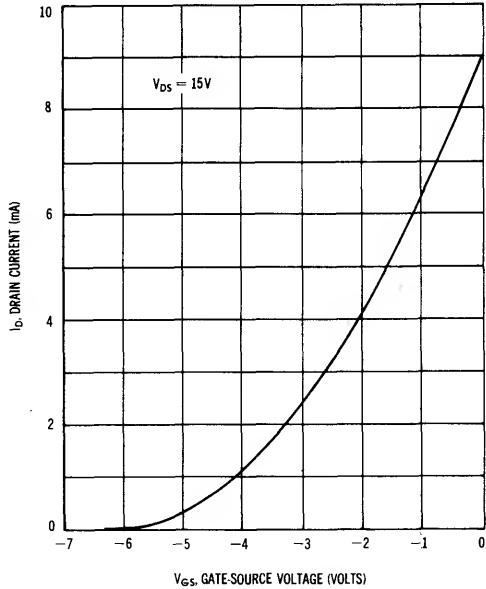
**FIGURE 6 — COMMON SOURCE TRANSFER CHARACTERISTICS**  
 $V_{GS(\text{off})} \approx -3.5 \text{ VOLTS}$



**FIGURE 7 — TYPICAL DRAIN CHARACTERISTICS**  
 $V_{GS(\text{off})} \approx -5.8 \text{ VOLTS}$



**FIGURE 8 — COMMON SOURCE TRANSFER CHARACTERISTICS**  
 $V_{GS(\text{off})} \approx -5.8 \text{ VOLTS}$



- NOTES:**
1. Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher  $|I_{DSS}|$  units reduces  $|I_{DSS}|$  (See Figure 10).
  2. Figures 8, 9, 10: Data taken in a standard printed circuit with a TO-18 type socket mounting and 1/4" lead length.